

SOT223 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

ISSUE 4 – JANUARY 1996 

FEATURES

- * High V_{CEO} and Low saturation voltages

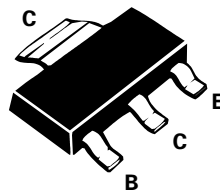
APPLICATIONS

- * Suitable for video output stages in TV sets
- * Switching power supplies

COMPLEMENTARY TYPE:- BFN36

PARTMARKING DETAIL:- BFN37

BFN37



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-250	V
Collector-Emitter Voltage	V_{CEO}	-250	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-500	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	-2	W
Operating and Storage Temperature Range	$T_J; T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-250			V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-250			V	$I_C = -1mA$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu A$
Collector Cut-Off Current	I_{CBO}			-100 -20	nA μA	$V_{CB} = -200V$ $V_{CB} = -200V$ †
Emitter Cut-Off Current	I_{EBO}			-100	nA	$V_{EB} = -4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.4	V	$I_C = -20mA$, $I_B = -2mA$ *
Base Emitter Saturation Voltage	$V_{BE(sat)}$			-0.9	V	$I_C = -20mA$, $I_B = -2mA$ *
Static Forward Current Transfer Ratio	h_{FE}	25 40 40				$I_C = -1mA$, $V_{CE} = -10V$ * $I_C = -10mA$, $V_{CE} = -10V$ * $I_C = -30mA$, $V_{CE} = 10V$ *
Transition Frequency	f_T		100		MHz	$I_C = -20mA$, $V_{CE} = -10V$ $f = 100MHz$
Output Capacitance	C_{obo}		2.5		pF	$V_{CB} = -30V$, $f = 1MHz$

† $T_{amb} = 150^{\circ}C$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
For typical characteristics graphs see FMMTA92 datasheet.